



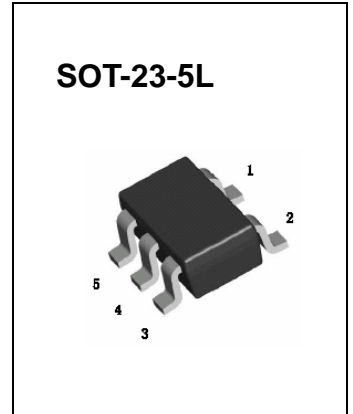
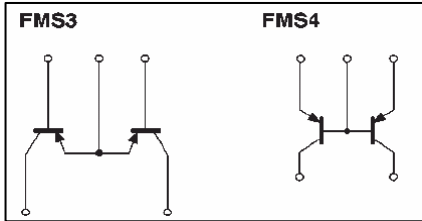
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-5L Plastic-Encapsulate Transistors

FMS3,FMS4 DUAL TRANSISTOR

FEATURES

High breakdown voltage



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Power Dissipation	0.3	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

MARKING: FMS3:S3 FMS4:S4

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-100\text{V}, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-2\text{mA}$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12\text{V}, I_C=-2\text{mA}, f=100\text{MHz}$		140		MHz

Typical Characteristics

FMS3 FMS4

